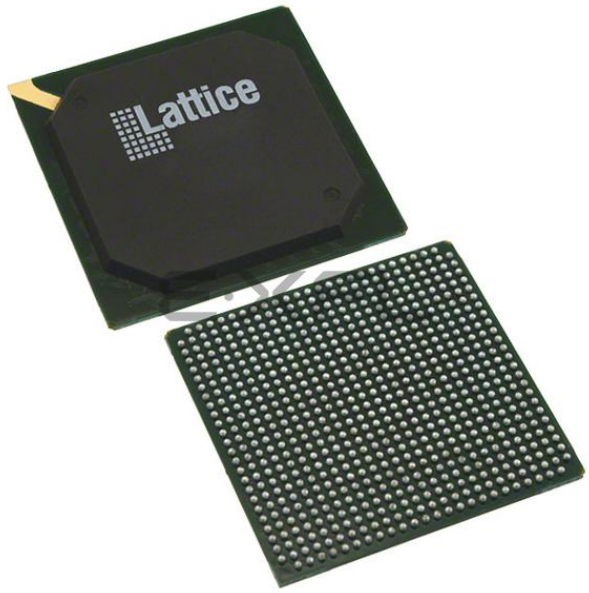
Lattice Semiconductor Corporation - LFE3-70E-6FN672C Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	8375
Number of Logic Elements/Cells	67000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-70e-6fn672c

LatticeECP3 Family Data Sheet Introduction

November 2009 Preliminary Data Sheet DS1021

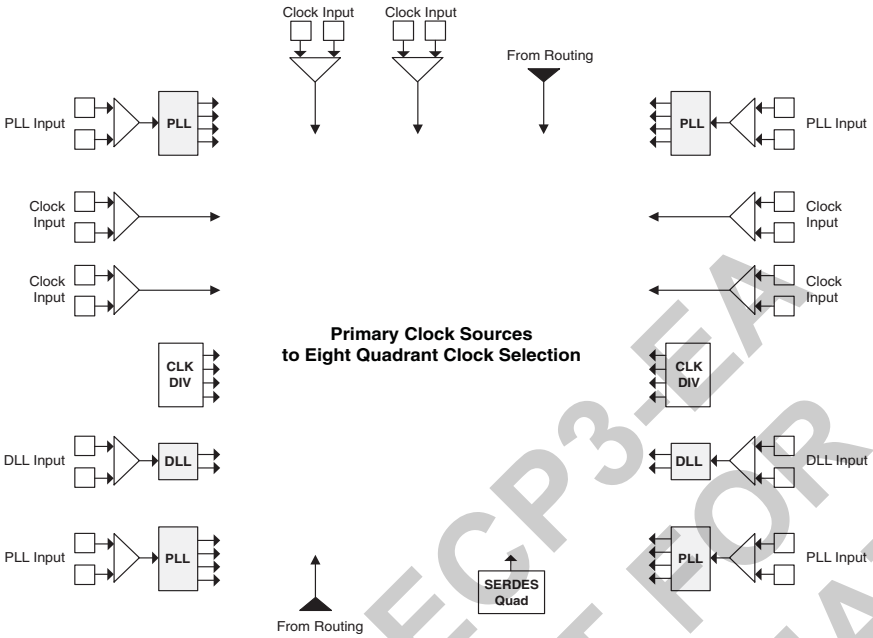
Features

- **Higher Logic Density for Increased System Integration**
  - 17K to 149K LUTs
  - 133 to 586 I/Os
- **Embedded SERDES**
  - 150 Mbps to 3.2 Gbps for Generic 8b10b, 10-bit SERDES, and 8-bit SERDES modes
  - Data Rates 230 Mbps to 3.2 Gbps per channel for all other protocols
  - Up to 16 channels per device: PCI Express, SONET/SDH, Ethernet (1GbE, SGMII, XAUI), CPRI, SMPTE 3G and Serial RapidIO
- **sysDSP™**
  - Fully cascadable slice architecture
  - 12 to 160 slices for high performance multiply and accumulate
  - Powerful 54-bit ALU operations
  - Time Division Multiplexing MAC Sharing
  - Rounding and truncation
  - Each slice supports
    - Half 36x36, two 18x18 or four 9x9 multipliers
    - Advanced 18x36 MAC and 18x18 Multiply-Multiply-Accumulate (MMAC) operations
- **Flexible Memory Resources**
  - Up to 6.85Mbits sysMEM™ Embedded Block RAM (EBR)
  - 36K to 303K bits distributed RAM
- **sysCLOCK Analog PLLs and DLLs**
  - Two DLLs and up to ten PLLs per device
- **Pre-Engineered Source Synchronous I/O**
  - DDR registers in I/O cells
  - Dedicated read/write levelling functionality
  - Dedicated gearing logic
  - Source synchronous standards support
    - ADC/DAC, 7:1 LVDS, XGMII
    - High Speed ADC/DAC devices
  - Dedicated DDR/DDR2/DDR3 memory with DQS support
  - Optional Inter-Symbol Interference (ISI) correction on outputs
- **Programmable sysI/O™ Buffer Supports Wide Range of Interfaces**
  - On-chip termination
  - Optional equalization filter on inputs
  - LVTTL and LVCMOS 33/25/18/15/12
  - SSTL 33/25/18/15 I, II
  - HSTL15 I and HSTL18 I, II
  - PCI and Differential HSTL, SSTL
  - LVDS, Bus-LVDS, LVPECL, RSDS, MLVDS
- **Flexible Device Configuration**
  - Dedicated bank for configuration I/Os
  - SPI boot flash interface
  - Dual-boot images supported
  - Slave SPI
  - TransFR™ I/O for simple field updates
  - Soft Error Detect embedded macro
- **System Level Support**
  - IEEE 1149.1 and IEEE 1532 compliant
  - Reveal Logic Analyzer
  - ORCAstra FPGA configuration utility
  - On-chip oscillator for initialization & general use
  - 1.2V core power supply

Table 1-1. LatticeECP3™ Family Selection Guide

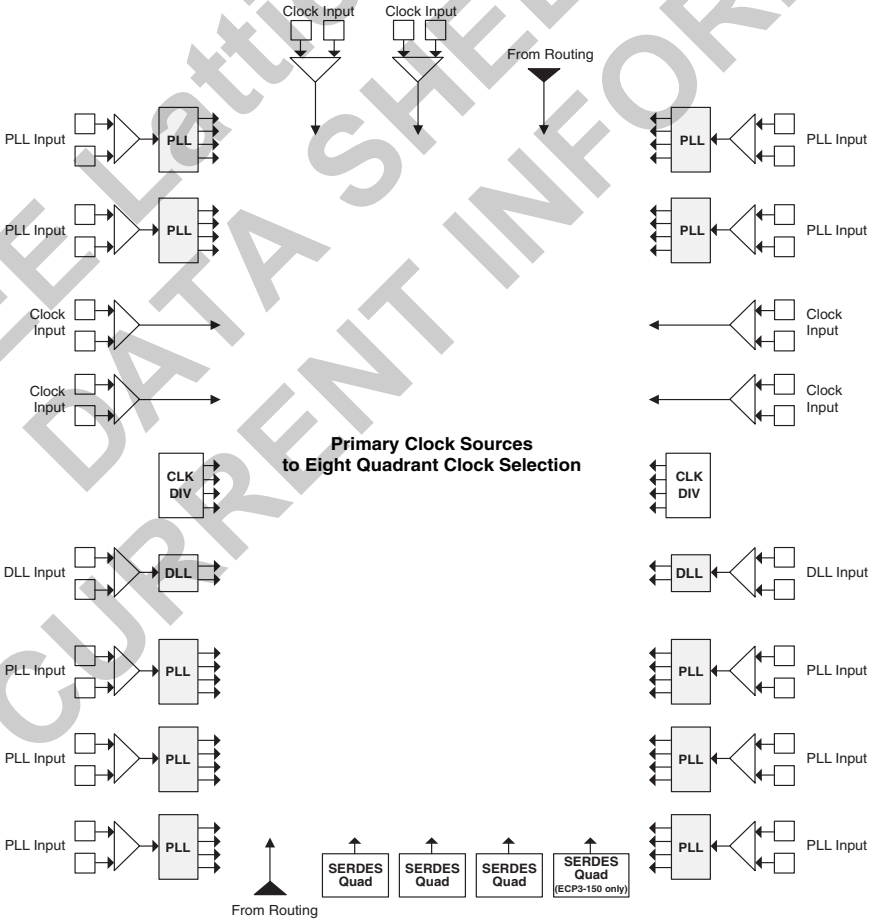
Device	ECP3-17	ECP3-35	ECP3-70	ECP3-95	ECP3-150
LUTs (K)	17	33	67	92	149
sysMEM Blocks (18Kbits)	38	72	240	240	372
Embedded Memory (Kbits)	700	1327	4420	4420	6850
Distributed RAM Bits (Kbits)	36	68	145	188	303
18X18 Multipliers	24	64	128	128	320
SERDES (Quad)	1	1	3	3	4
PLLs/DLLs	2 / 2	4 / 2	10 / 2	10 / 2	10 / 2
Packages and SERDES Channels/ I/O Combinations					
256 ftBGA (17x17 mm)	4 / 133	4 / 133			
484 fpBGA (23x23 mm)	4 / 222	4 / 295	4 / 295	4 / 295	
672 fpBGA (27x27 mm)		4 / 310	8 / 380	8 / 380	8 / 380
1156 fpBGA (35x35 mm)			12 / 490	12 / 490	16 / 586

Figure 2-10. Primary Clock Sources for LatticeECP3-35



Note: Clock inputs can be configured in differential or single-ended mode.

Figure 2-11. Primary Clock Sources for LatticeECP3-70, -95, -150



Note: Clock inputs can be configured in differential or single-ended mode.

Figure 2-20. Sources of Edge Clock (Left and Right Edges)

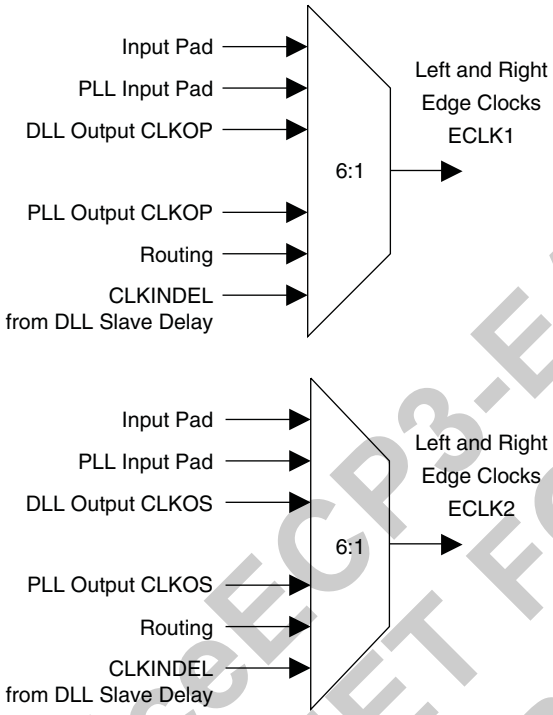
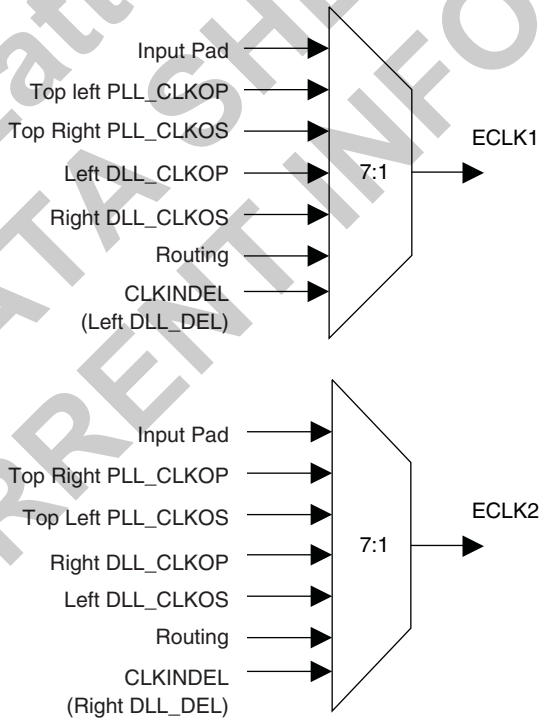


Figure 2-21. Sources of Edge Clock (Top Edge)



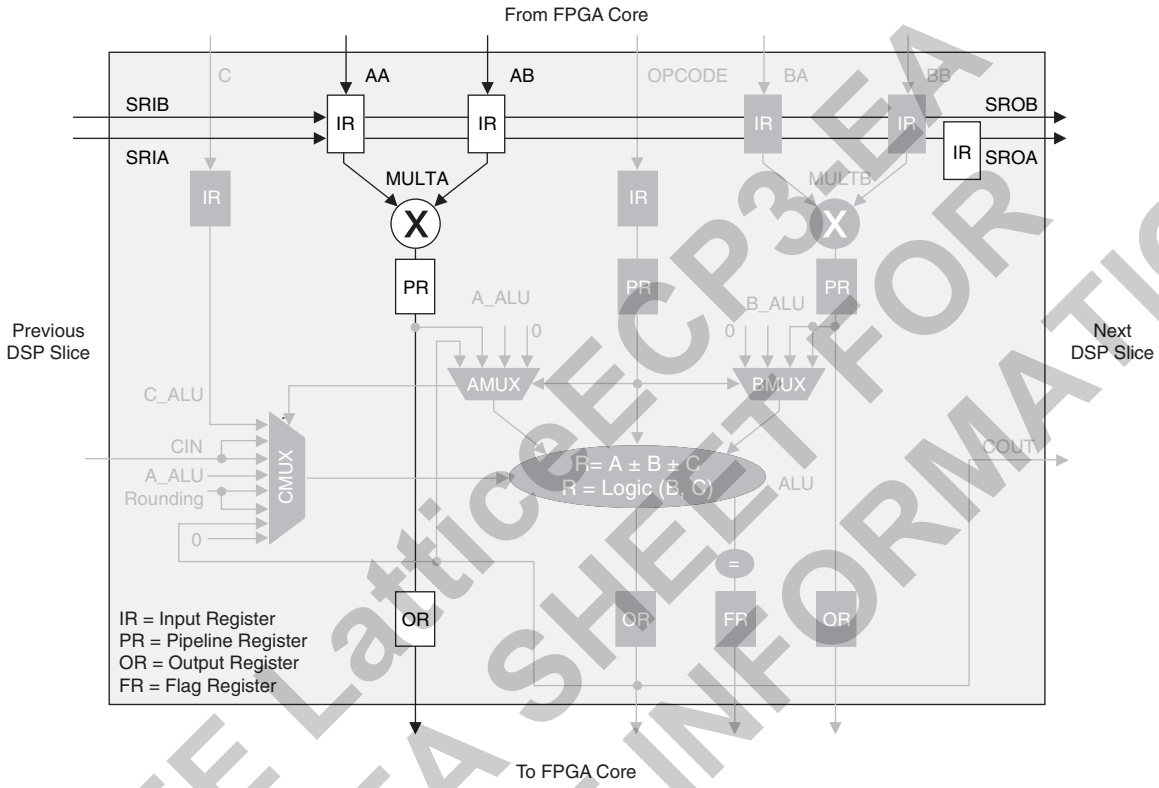
The edge clocks have low injection delay and low skew. They are used to clock the I/O registers and thus are ideal for creating I/O interfaces with a single clock signal and a wide data bus. They are also used for DDR Memory or Generic DDR interfaces.

For further information, please refer to TN1182, LatticeECP3 sysDSP Usage Guide.

MULT DSP Element

This multiplier element implements a multiply with no addition or accumulator nodes. The two operands, AA and AB, are multiplied and the result is available at the output. The user can enable the input/output and pipeline registers. Figure 2-26 shows the MULT sysDSP element.

Figure 2-26. MULT sysDSP Element



MULTADDSUB DSP Element

In this case, the operands AA and AB are multiplied and the result is added/subtracted with the result of the multiplier operation of operands BA and BB. The user can enable the input, output and pipeline registers. Figure 2-29 shows the MULTADDSUB sysDSP element.

Figure 2-29. MULTADDSUB

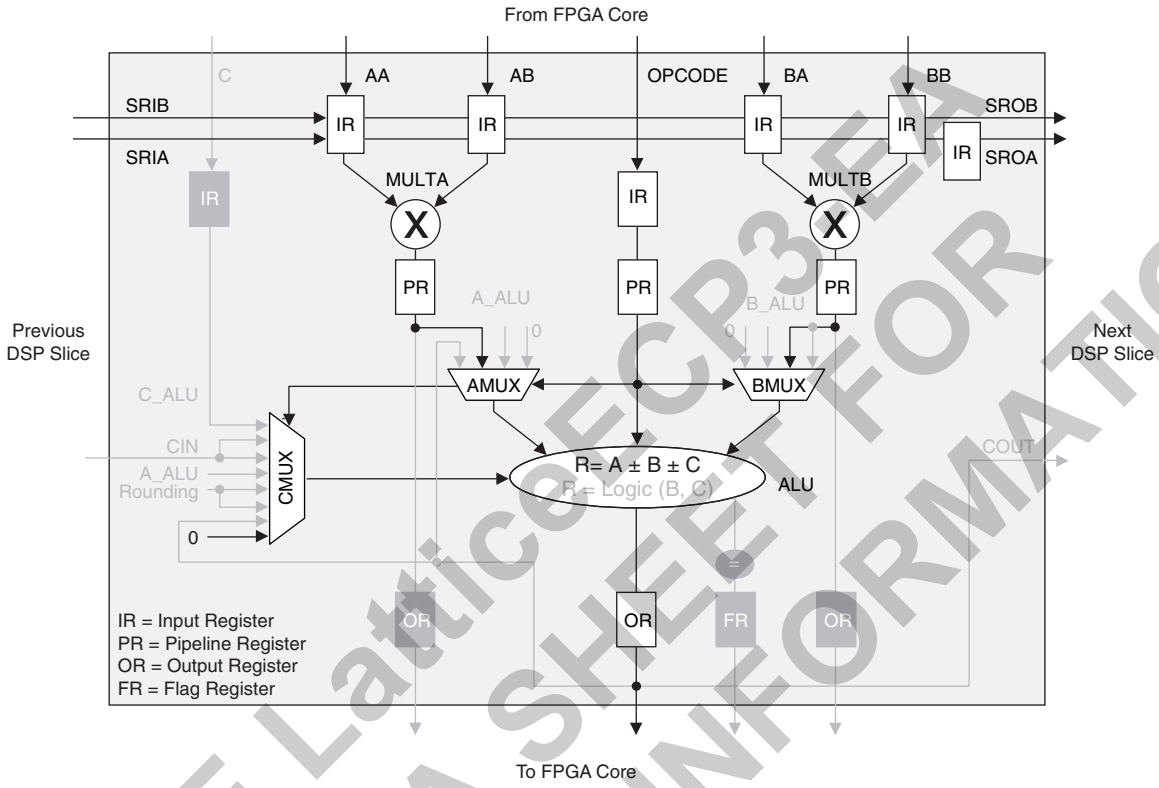
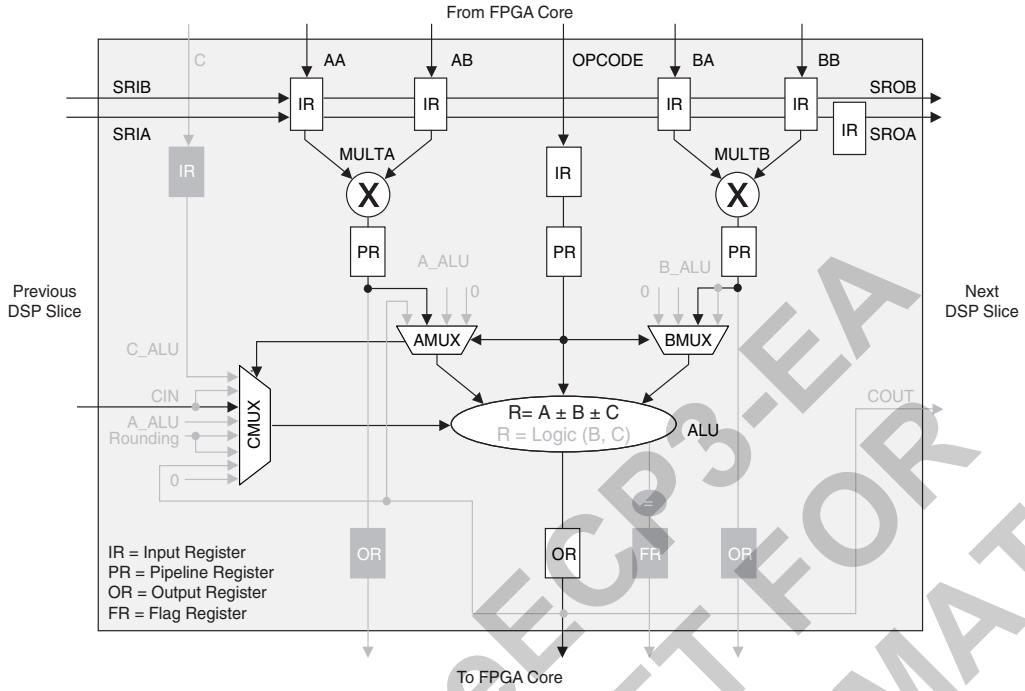


Figure 2-31. MULTADDSUBSUM Slice 1



Advanced sysDSP Slice Features

Cascading

The LatticeECP3 sysDSP slice has been enhanced to allow cascading. Adder trees are implemented fully in sysDSP slices, improving the performance. Cascading of slices uses the signals CIN, COUT and C Mux of the slice.

Addition

The LatticeECP3 sysDSP slice allows for the bypassing of multipliers and cascading of adder logic. High performance adder functions are implemented without the use of LUTs. The maximum width adders that can be implemented are 54-bit.

Rounding

The rounding operation is implemented in the ALU and is done by adding a constant followed by a truncation operation. The rounding methods supported are:

- Rounding to zero (RTZ)
- Rounding to infinity (RTI)
- Dynamic rounding
- Random rounding
- Convergent rounding

(referred to as DQS) is not free-running so this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The delay required for the DQS signal is generated by two dedicated DLLs (DDR DLL) on opposite side of the device. Each DLL creates DQS delays in its half of the device as shown in Figure 2-36. The DDR DLL on the left side will generate delays for all the DQS Strobe pins on Banks 0, 7 and 6 and DDR DLL on the right will generate delays for all the DQS pins on Banks 1, 2 and 3. The DDR DLL loop compensates for temperature, voltage and process variations by using the system clock and DLL feedback loop. DDR DLL communicates the required delay to the DQS delay block using a 7-bit calibration bus (DCNTL[6:0])

The DQS signal (selected PIOs only, as shown in Figure 2-35) feeds from the PAD through a DQS control logic block to a dedicated DQS routing resource. The DQS control logic block consists of DQS Read Control logic block that generates control signals for the read side and DQS Write Control logic that generates the control signals required for the write side. A more detailed DQS control diagram is shown in Figure 2-37, which shows how the DQS control blocks interact with the data paths.

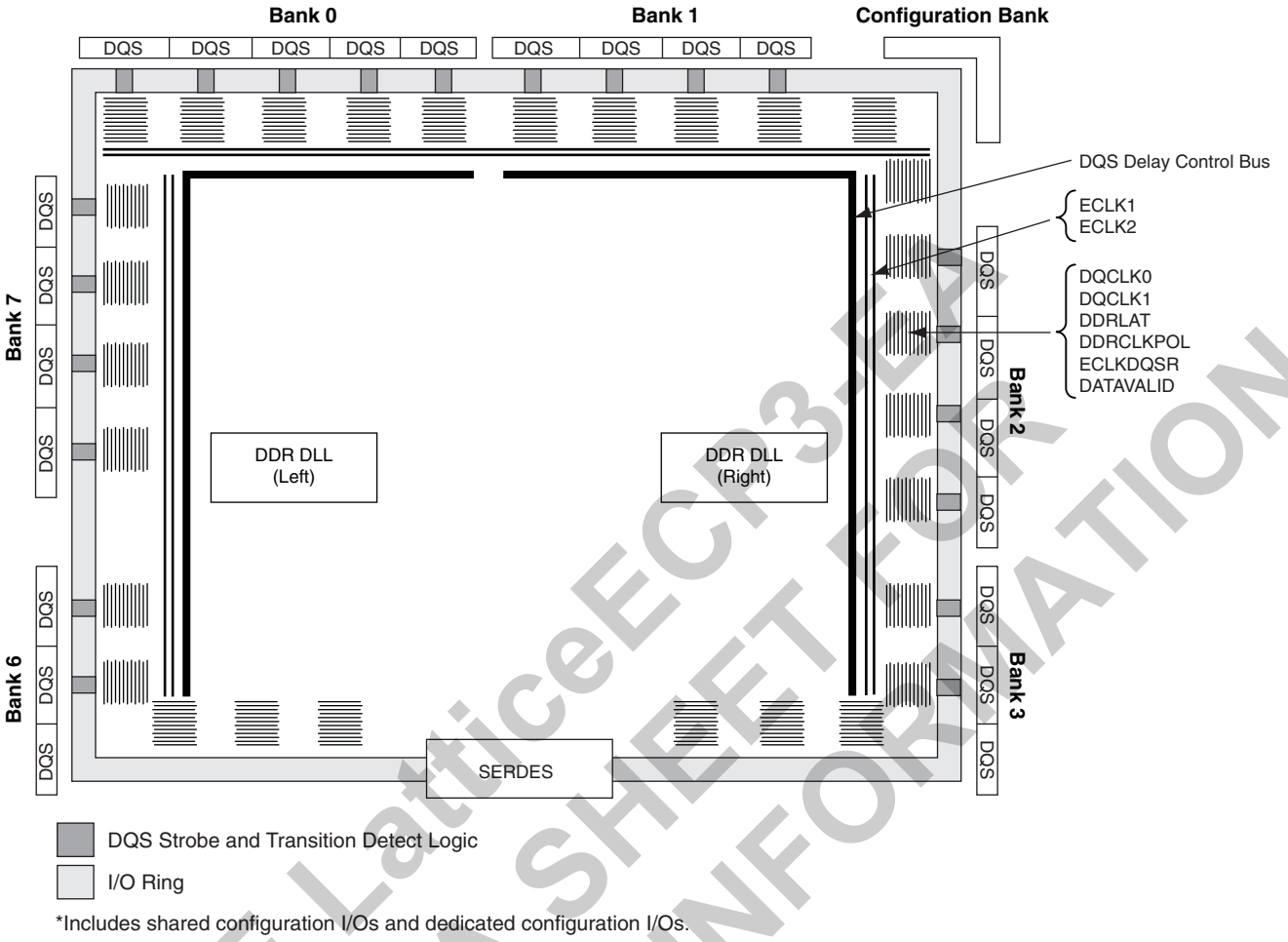
The DQS Read control logic receives the delay generated by the DDR DLL on its side and delays the incoming DQS signal by 90 degrees. This delayed ECLKDQSR is routed to 10 or 11 DQ pads covered by that DQS signal. This block also contains a polarity control logic that generates a DDRCLKPOL signal, which controls the polarity of the clock to the sync registers in the input register blocks. The DQS Read control logic also generates a DDRLAT signal that is in the input register block to transfer data from the first set of DDR register to the second set of DDR registers when using the DDRX2 gearbox mode for DDR3 memory interface.

The DQS Write control logic block generates the DQCLK0 and DQCLK1 clocks used to control the output gearing in the Output register block which generates the DDR data output and the DQS output. They are also used to control the generation of the DQS output through the DQS output register block. In addition to the DCNTL [6:0] input from the DDR DLL, the DQS Write control block also uses a Dynamic Delay DYN DEL [7:0] attribute which is used to further delay the DQS to accomplish the write leveling found in DDR3 memory. Write leveling is controlled by the DDR memory controller implementation. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock. This will generate the DQSW signal used to generate the DQS output in the DQS output register block.

Figure 2-36 and Figure 2-37 show how the DQS transition signals that are routed to the PIOs.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

Figure 2-36. Edge Clock, DLL Calibration and DQS Local Bus Distribution



Hot Socketing Specifications[1, 3, 4]

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
IDK_HS[2]	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH}$ (Max.)	—	—	+/-1	mA
IDK[5]	Input or I/O Leakage Current	$0 \le V_{IN} < V_{CCIO}$	—	—	+/-1	mA
		$V_{CCIO} \le V_{IN} \le V_{CCIO}$ + 0.5V	—	18	—	mA

1. V_{CC}, V_{CCAUX} and V_{CCIO} should rise/fall monotonically.
2. Applicable to general purpose I/O pins in top I/O banks only.
3. I_{DK} is additive to I_{PU}, I_{PW} or I_{BH}.
4. LVCMOS and LVTTL only.
5. Applicable to general purpose I/O pins in left and right I/O banks only.

Hot Socketing Requirements[1, 2]

Description	Min.	Typ.	Max.	Units
Input current per SERDES I/O pin when device is powered down and inputs driven.	—	—	8	mA

1. Assumes the device is powered down, all supplies grounded, both P and N inputs driven by CML driver with maximum allowed VCCOB (1.575V), 8b10b data, internal AC coupling.
2. Each P and N input must have less than the specified maximum input current. For a 16-channel device, the total input current would be 8mA*16 channels *2 input pins per channel = 256mA

ESD Performance

Pin Group	ESD Stress	Min.	Units
All pins	HBM	1000	V
All pins except high-speed serial and XRES[1]	CDM	500	V
High-speed serial inputs	CDM	400	V

1. The XRES pin on the TW device passes CDM testing at 250V.

LatticeECP3 External Switching Characteristics [1, 2]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clock[6]									
f_{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-150EA	—	500	—	420	—	375	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-150EA	—	300	—	330	—	360	ps
t_{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-150EA	—	250	—	280	—	300	ps
t_{W_PRI}	Frequency for Primary Clock Tree	ECP3-70E/95E	—	500	—	420	—	375	MHz
f_{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-70E/95E	0.8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-70E/95E	—	300	—	330	—	360	ps
t_{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-70E/95E	—	250	—	280	—	300	ps
Edge Clock[6]									
f_{MAX_EDGE}	Frequency for Edge Clock	ECP3-150EA	—	500	—	420	—	375	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-150EA	0.9	—	1.0	—	1.2	—	ns
$t_{SKEW\_EDGE\_DQS}$	Edge Clock Skew Within an Edge of the Device	ECP3-150EA	—	200	—	210	—	220	ps
f_{MAX_EDGE}	Frequency for Edge Clock	ECP3-70E/95E	—	500	—	420	—	375	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-70E/95E	0.9	—	1.0	—	1.2	—	ns
$t_{SKEW\_EDGE\_DQS}$	Edge Clock Skew Within an Edge of the Device	ECP3-70E/95E	—	200	—	225	—	250	ps

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic SDR									
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock Without PLL[2]									
t_{CO}	Clock to Output - PIO Output Register	ECP3-150EA	—	4.0	—	4.4	—	4.8	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-150EA	1.6	—	1.8	—	2.1	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.2	—	1.3	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	0.1	—	0.1	—	0.1	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-150EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-70E/95E	—	3.9	—	4.3	-—	4.7	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-70E/95E	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-70E/95E	1.5	—	1.8	—	2.0	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70E/95E	1.3	—	1.5	—	1.8	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70E/95E	0.0	—	0.0	—	0.0	—	ns

LatticeECP3 External Switching Characteristics (Continued)[1, 2]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-70E/95E	0.765	—	0.765	—	0.765	—	UI
f_{MAX_GDDR}	DDR/DDRX2 Clock Frequency[8]	ECP3-70E/95E	—	500	—	420	—	375	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX2_RX.DQS.Centered) using DQS Pin for Clock Input									
Left and Right Sides									
t_{SUGDDR}	Data Setup Before CLK	ECP3-150EA		—		—		—	ns
t_{HGDDR}	Data Hold After CLK	ECP3-150EA		—		—		—	ns
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—		—		—		ns
Generic DDRX2 Inputs with Clock and Data (<10 Bits Side) Aligned at Pin (GDDRX2_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Left and Right Sides									
$t_{DVACLKGDDR}$	Data Setup Before CLK (Left and Right Side)	ECP3-150EA	—		—		—		
$t_{DVECLKGDDR}$	Data Hold After CLK (Left and Right Side)	ECP3-150EA		—		—		—	
f_{MAX_GDDR}	DDRX2 Clock Frequency (Left and Right Side)	ECP3-150EA	—		—		—		
Generic DDRX1 Output with Clock and Data (>10 Bits Wide) Centered at Pin (GDDRX1_TX.SCLK.Centered)									
Left, Right and Top Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA		—		—		—	
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA		—		—		—	
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—		—		—		
Generic DDRX1 Outputs with clock in the center of data window, with PLL 90-degree shifted clock ouput (GDDRX1_TX.ECLK.Centered)									
$t_{DIBGDDR}$	Data Invalid Before CLK	ECP3-70E/95E	670	—	670	—	670	—	ps
$t_{DIAGDDR}$	Data Invalid After CLK	ECP3-70E/95E	670	—	670	—	670	—	ps
fMAX_GDDR	DDRX1 Clock Frequency	ECP3-70E/95E	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data (> 10 Bits Wide) Aligned at Pin (GDDRX1_TX.SCLK.Aligned)									
Left, Right and Top Sides									
$t_{DIBGDDR}$	Data Hold After CLK	ECP3-150EA	—		—		—		
$t_{DIAGDDR}$	Data Setup Before CLK	ECP3-150EA	—		—		—		
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—		—		—		
Generic DDRX1 Outputs with clock and data edge aligned, without PLL									
$t_{DIBGDDR}$	Data Invalid Before CLK	ECP3-70E/95E	—	330	—	330	—	330	ps
$t_{DIAGDDR}$	Data Invalid After CLK	ECP3-70E/95E	—	330	—	330	—	330	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70E/95E	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX1_TX.DQS.Centered)									
Left, Right and Top Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA	—		—		—		
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA	—		—		—		
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—		—		—		

Figure 3-7. DDR/DDR2/DDR3 SDRAM

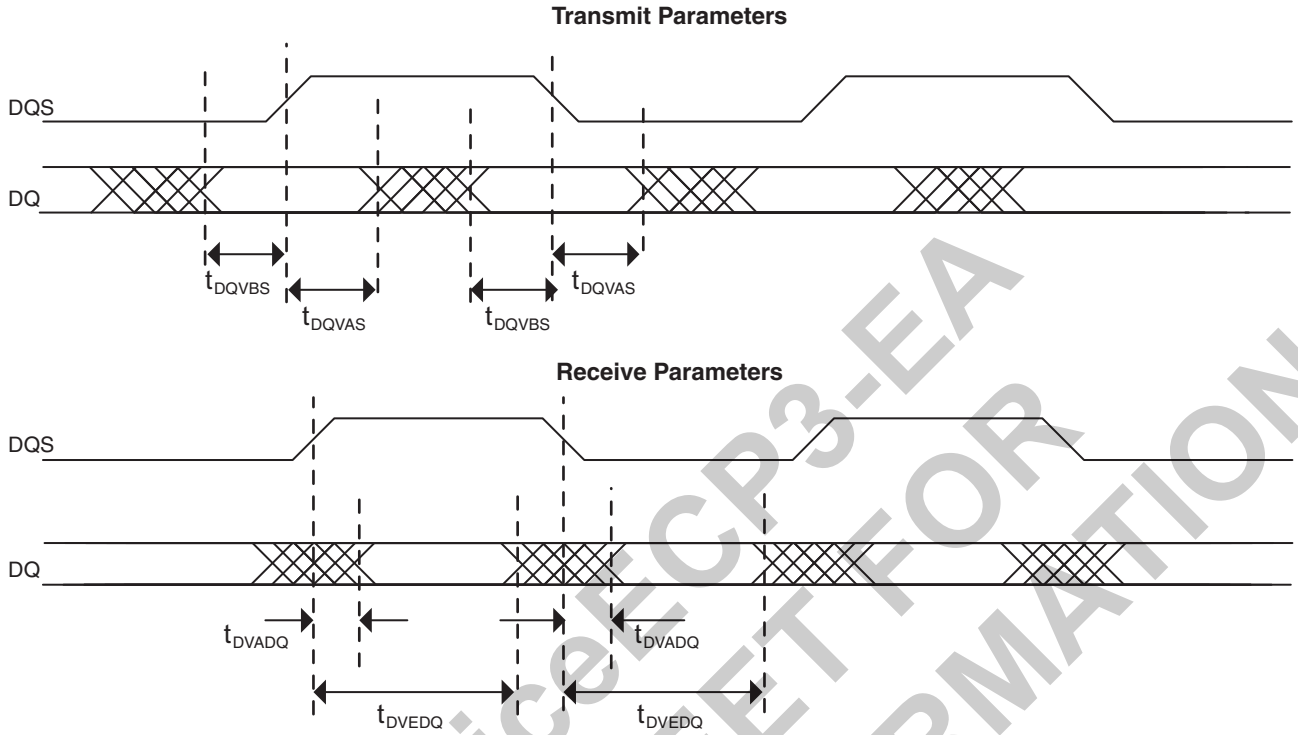
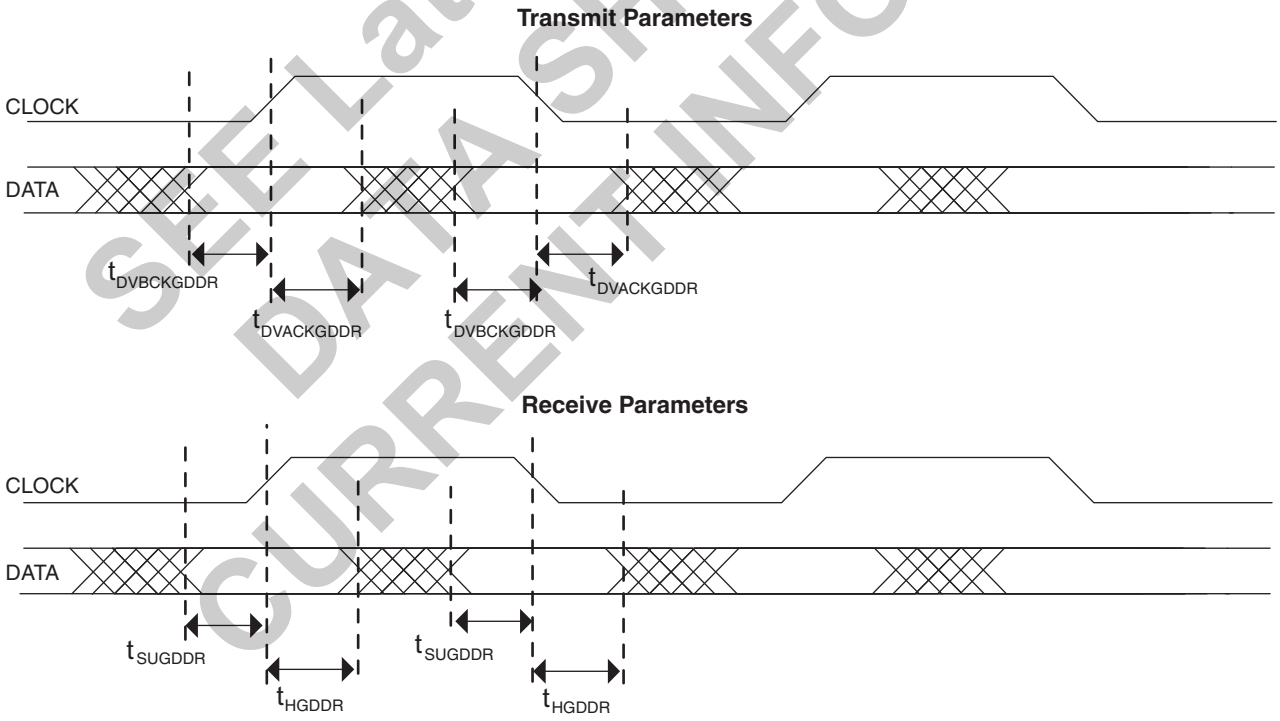


Figure 3-8. Generic DDR/DDR2 Parameters (With Clock Center on Data Window)



SERDES High Speed Data Receiver

Table 3-9. Serial Input Data Specifications

Symbol	Description		Min.	Typ.	Max.	Units
$RX\text{-}CID_S$	Stream of nontransitions[1] (CID = Consecutive Identical Digits) @ 10^{-12} BER	3.125G	—	—	136	Bits
		2.5G	—	—	144	
		1.485G	—	—	160	
		622M	—	—	204	
		270M	—	—	228	
		155M	—	—	296	
$V_{RX\text{-}DIFF\text{-}S}$	Differential input sensitivity		150	—	1760	mV, p-p
$V_{RX\text{-}IN}$	Input levels		0	—	V_{CCA} +0.5[4]	V
$V_{RX\text{-}CM\text{-}DC}$	Input common mode range (DC coupled)		0.6	—	V_{CCA}	V
$V_{RX\text{-}CM\text{-}AC}$	Input common mode range (AC coupled)[3]		0.1	—	V_{CCA} +0.2	V
$T_{RX\text{-}RELOCK}$	SCDR re-lock time[2]		—	1000	—	Bits
$Z_{RX\text{-}TERM}$	Input termination 50/75 Ohm/High Z		-20%	50/75/HiZ	+20%	Ohms
$RL_{RX\text{-}RL}$	Return loss (without package)		10	—	—	dB

1. This is the number of bits allowed without a transition on the incoming data stream when using DC coupling.
2. This is the typical number of bit times to re-lock to a new phase or frequency within +/- 300 ppm, assuming 8b10b encoded data.
3. AC coupling is used to interface to LVPECL and LVDS. LVDS interfaces are found in laser drivers and Fibre Channel equipment. LVDS interfaces are generally found in 622 Mbps SERDES devices.
4. Up to 1.76V.

Input Data Jitter Tolerance

A receiver's ability to tolerate incoming signal jitter is very dependent on jitter type. High speed serial interface standards have recognized the dependency on jitter type and have specifications to indicate tolerance levels for different jitter types as they relate to specific protocols. Sinusoidal jitter is considered to be a worst case jitter type.

Table 3-10. Receiver Total Jitter Tolerance Specification

Description	Frequency	Condition	Min.	Typ.	Max.	Units
Deterministic	3.125 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	2.5 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	1.25 Gbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p
Deterministic	622 Mbps	600 mV differential eye	—	—	0.47	UI, p-p
Random		600 mV differential eye	—	—	0.18	UI, p-p
Total		600 mV differential eye	—	—	0.65	UI, p-p

Note: Values are measured with CJPAT, all channels operating, FPGA Logic active, I/Os around SERDES pins quiet, voltages are nominal, room temperature.

SERDES External Reference Clock

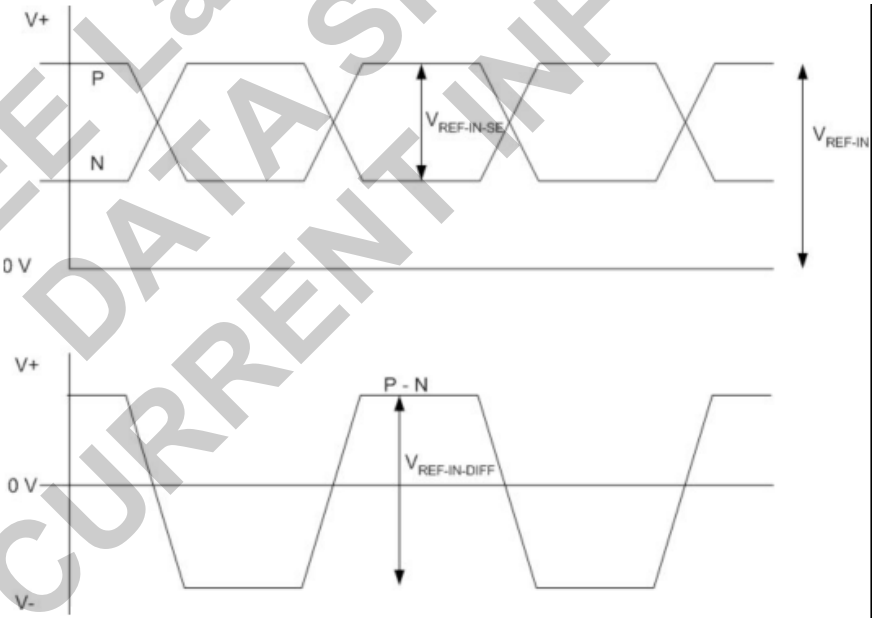
The external reference clock selection and its interface are a critical part of system applications for this product. Table 3-12 specifies reference clock requirements, over the full range of operating conditions.

Table 3-12. External Reference Clock Specification (refclkp/refclkn)

Symbol	Description	Min.	Typ.	Max.	Units
F_{REF}	Frequency range	15	—	320	MHz
$F_{REF-PPM}$	Frequency tolerance[4]	-1000	—	1000	ppm
$V_{REF-IN-SE}$	Input swing, single-ended clock[1]	200	—	V_{CCA}	mV, p-p
$V_{REF-IN-DIFF}$	Input swing, differential clock	200	—	$2*V_{CCA}$	mV, p-p differential
V_{REF-IN}	Input levels	0	—	V_{CCA} + 0.3	V
$V_{REF-CM-AC}$	Input common mode range (AC coupled)[2]	0.125	—	V_{CCA}	V
D_{REF}	Duty cycle[3]	40	—	60	%
T_{REF-R}	Rise time (20% to 80%)	200	500	1000	ps
T_{REF-F}	Fall time (80% to 20%)	200	500	1000	ps
$Z_{REF-IN-TERM-DIFF}$	Differential input termination	-20%	100/2K	+20%	Ohms
$C_{REF-IN-CAP}$	Input capacitance	—	—	7	pF

1. The signal swing for a single-ended input clock must be as large as the p-p differential swing of a differential input clock to get the same gain at the input receiver. Lower swings for the clock may be possible, but will tend to increase jitter.
2. When AC coupled, the input common mode range is determined by:
(Min input level) + (Peak-to-peak input swing)/2 ≤ (Input common mode voltage) ≤ (Max input level) - (Peak-to-peak input swing)/2
3. Measured at 50% amplitude.
4. Depending on the application, the PLL_LOL_SET and CDR_LOL_SET control registers may be adjusted for other tolerance values as described in TN1176, LatticeECP3 SERDES/PCS Usage Guide.

Figure 3-13. SERDES External Reference Clock Waveforms



Gigabit Ethernet/Serial Rapid I/O Type 1/SGMII Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-17. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[3, 4, 5]	Output data deterministic jitter		—	—	0.10	UI
J_{TX_TJ}[2, 3, 4, 5]	Total output data jitter		—	—	0.24	UI

1. Rise and fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-ohm impedance (100-ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 1.25 Gbps.

Table 3-18. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 1.25 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 1.25 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[1, 2, 3, 4, 5]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.34	UI
J_{RX_RJ}[1, 2, 3, 4, 5]	Random jitter tolerance (peak-to-peak)		—	—	0.26	UI
J_{RX_SJ}[1, 2, 3, 4, 5]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.11	UI
J_{RX_TJ}[1, 2, 3, 4, 5]	Total jitter tolerance (peak-to-peak)		—	—	0.71	UI
T_{RX_EYE}	Receiver eye opening		0.29	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-14.
2. Jitter values are measured with each high-speed input AC coupled into a 50-ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 1.25 Gbps.

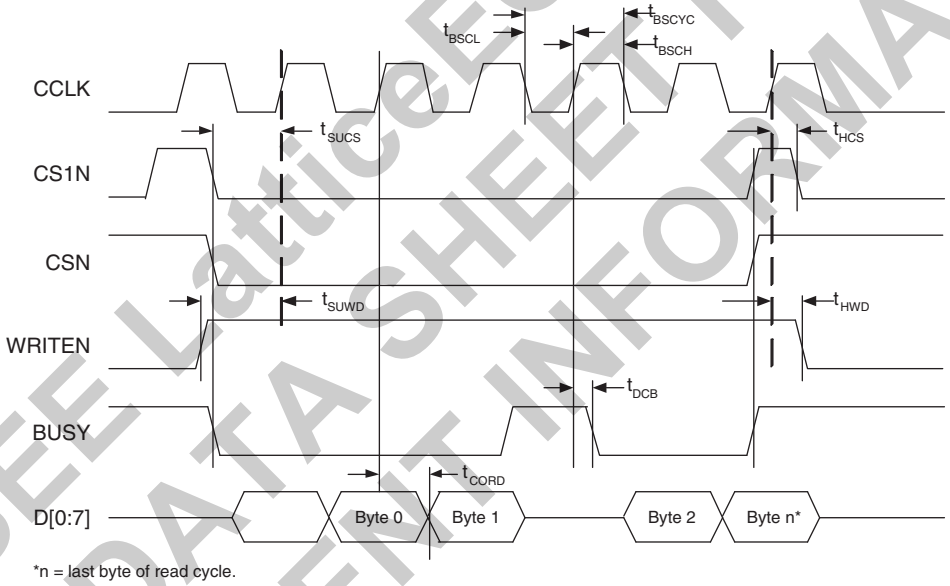
LatticeECP3 sysCONFIG Port Timing Specifications (Continued)

Over Recommended Operating Conditions

Parameter	Description	Min.	Max.	Units
t_{CHHH}	HOLDN Low Hold Time (Relative to CCLK)	5	—	ns
Master and Slave SPI (Continued)				
t_{CHHL}	HOLDN High Hold Time (Relative to CCLK)	5	—	ns
t_{HHCH}	HOLDN High Setup Time (Relative to CCLK)	5	—	ns
t_{HLQZ}	HOLDN to Output High-Z	—	9	ns
t_{HHQX}	HOLDN to Output Low-Z	—	9	ns

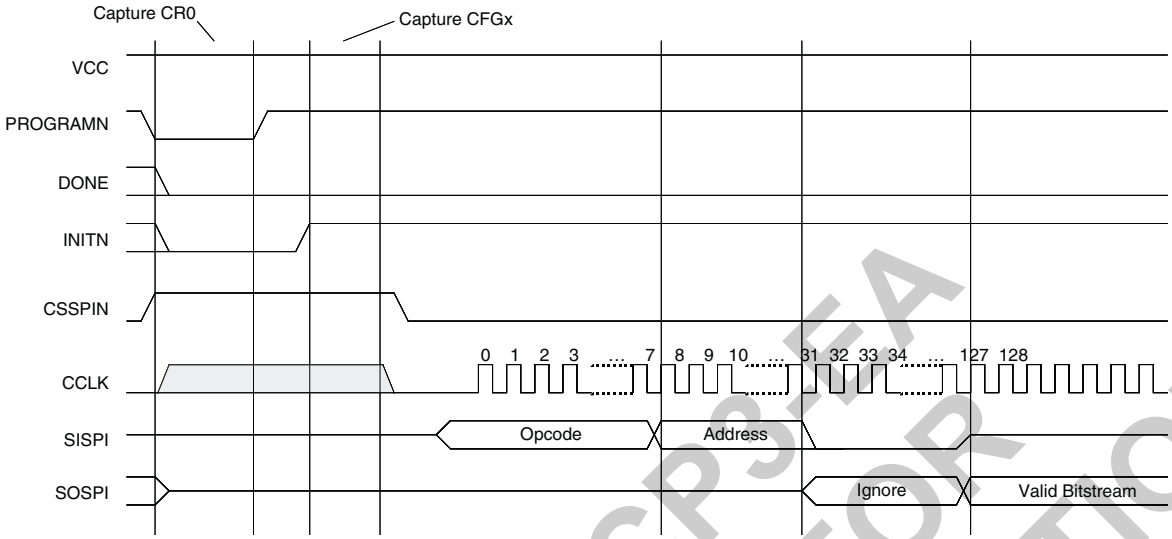
Parameter	Min.	Max.	Units
Master Clock Frequency	Selected value - 15%	Selected value + 15%	MHz
Duty Cycle	40	60	%

Figure 3-16. sysCONFIG Parallel Port Read Cycle



*n = last byte of read cycle.

Figure 3-24. Master SPI Configuration Waveforms



PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
For Top Edge of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ

Note: “n” is a row PIC number.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-95E			ECP3-95EA			ECP3-150EA	
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	484 fpBGA	672 fpBGA	1156 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43	21	30	43	30	47
	Bank 1	18	24	39	18	24	39	24	43
	Bank 2	10	15	16	8	12	13	12	18
	Bank 3	23	27	39	20	23	33	23	37
	Bank 6	26	30	39	22	25	33	25	37
	Bank 7	14	20	22	11	16	18	16	24
	Bank 8	12	12	12	12	12	12	12	12
Highspeed Differential I/O per Bank	Bank 0	0	0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0	0	0
	Bank 2	4	6	6	6	9	9	9	15
	Bank 3	6	8	10	9	12	16	12	21
	Bank 6	7	9	10	11	14	16	14	21
	Bank 7	6	8	9	9	12	13	12	18
	Bank 8	0	0	0	0	0	0	0	0
Total Single Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43	42/21	60/30	86/43	60/30	94/47
	Bank 1	36/18	48/24	78/39	36/18	48/24	78/39	48/24	86/43
	Bank 2	28/14	42/21	44/22	28/14	42/21	44/22	42/21	66/33
	Bank 3	58/29	71/35	98/49	58/29	71/35	98/49	71/35	116/58
	Bank 6	67/33	78/39	98/49	67/33	78/39	98/49	78/39	116/58
	Bank 7	40/20	56/28	62/31	40/20	56/28	62/31	56/28	84/42
	Bank 8	24/12	24/12	24/12	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank	Bank 0	3	5	7	3	5	7	5	7
	Bank 1	3	4	7	3	4	7	4	7
	Bank 2	2	3	3	2	3	3	3	4
	Bank 3	3	4	5	3	4	5	4	7
	Bank 6	4	4	5	4	4	5	4	7
	Bank 7	3	4	4	3	4	4	4	6
	Configuration Bank8	0	0	0	0	0	0	0	0
SERDES Quads		1	2	3	1	2	3	2	4

1.These pins must remain floating on the board.

Date	Version	Section	Change Summary
May 2009 (cont.)	01.1 (cont.)	DC and Switching Characteristics (cont.)	Updated timing information
			Updated SERDES minimum frequency.
			Added data to the following tables: External Switching Characteristics, Internal Switching Characteristics, Family Timing Adders, Maximum I/O Buffer Speed, DLL Timing, High Speed Data Transmitter, Channel Output Jitter, Typical Building Block Function Performance, Register-to-Register Performance, and Power Supply Requirements.
			Updated Serial Input Data Specifications table.
			Updated Transmit table, Serial Rapid I/O Type 2 Electrical and Timing Characteristics section.
		Pinout Information	Updated Signal Description tables.
			Updated Pin Information Summary tables and added footnote 1.
July 2009	01.2	Multiple	Changed references of “multi-boot” to “dual-boot” throughout the data sheet.
		Architecture	Updated On-Chip Programmable Termination bullets.
			Updated On-Chip Termination Options for Input Modes table.
			Updated On-Chip Termination figure.
		DC and Switching Characterisitcs	Changed min/max data for FREF_PPM and added footnote 4 in SERDES External Reference Clock Specification table.
			Updated SERDES minimum frequency.
		Pinout Information	Corrected MCLK to be I/O and CCLK to be I in Signal Descriptions table
August 2009	01.3	DC and Switching Characterisitcs	Corrected truncated numbers for V_{CCIB} and V_{CCOB} in Recommended Operating Conditions table.
September 2009	01.4	Architecture	Corrected link in sysMEM Memory Block section.
			Updated information for On-Chip Programmable Termination and modified corresponding figure.
			Added footnote 2 to On-Chip Programmable Termination Options for Input Modes table.
			Corrected Per Quadrant Primary Clock Selection figure.
		DC and Switching Characterisitcs	Modified -8 Timing data for 1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers)
			Added ESD Performance table.
			LatticeECP3 External Switching Characteristics table - updated data for $t_{DIBGDDR}$, t_{W_PRI}, t_{W_EDGE} and $t_{SKEW\_EDGE\_DQS}$.
			LatticeECP3 Internal Switching Characteristics table - updated data for t_{COO_PIO} and added footnote #4.
			sysCLOCK PLL Timing table - updated data for f_{OUT}.
			External Reference Clock Specification (refclkp/refclkn) table - updated data for $V_{REF-IN-SE}$ and $V_{REF-IN-DIFF}$.
			LatticeECP3 sysCONFIG Port Timing Specifications table - updated data for t_{MWC}.
			Added TRLVDS DC Specification table and diagram.
			Updated Mini LVDS table.
November 2009	01.5	Introduction	Updated Embedded SERDES features.
			Added SONET/SDH to Embedded SERDES protocols.
		Architecture	Updated Figure 2-4, General Purpose PLL Diagram.
			Updated SONET/SDH to SERDES and PCS protocols.